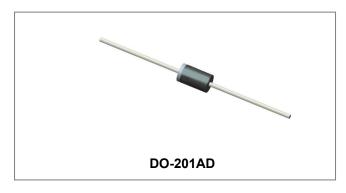


#### Technical Data Data Sheet N1820, Rev. A





# **SB20100 SCHOTTKY RECTIFIER**



#### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- · Reverse battery protection
- Disk drives
- Battery charging

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>C</sub> =105°C, rectangular wave form	20	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse, T <sub>C</sub> =25°C	280	Α

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	V <sub>F1</sub> @ 20A, Pulse, T <sub>J</sub> = 25 °C		0.93	V
	$V_{F2}$	@ 20A, Pulse, T <sub>J</sub> = 125 °C	-	0.80	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 25 °C	-	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 125 °C	-	10	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	-	500	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body 8.0 -		-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com
     sales@ smc-diodes.com



**Technical Data** Data Sheet N1820, Rev. A

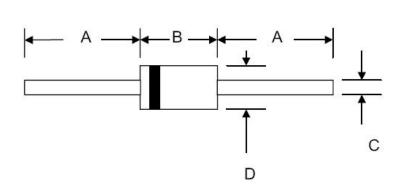




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to case	$R_{ heta JC}$	DC operation	4.5	°C/W
Approximate Weight	wt	-	1.02	g

#### **Mechanical Dimensions DO-201AD**



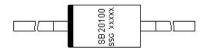
CYMPOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	8.50	9.50	0.335	0.374	
С	1.2	1.3	0.048	0.052	
D	5.0	5.6	0.197	0.220	

## **Ordering Information**

Device	Package	Shipping	
SB20100	DO-201AD	1250noo / tono	
3B20100	(Pb-Free)	1250pcs / tape	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

SB20100 SSG ΥY

= Part Name = SSG

= Year WW

= Week = Lot Number

<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

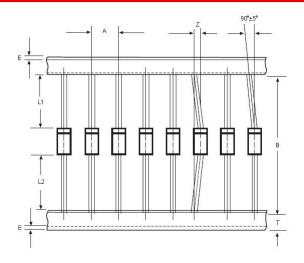


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#### Carrier Tape Specification DO-201AD



SYMBOL	Millimeters		
	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

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